On the Possibility of Experim ental Veri cation of Som e Localization Theory Predictions

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A bstract

The spatial non {locallity (dispersion) of the transport equations results in a nonlinear dependence of the voltage drop U on the distance between the points of measuring. Therefore the results of the usual two {probe measurements of the conductivity dependessentially on the relation between the sample linear size L and the spatial dispersion scale R of the generalized dispersion scale R of the generalized dispersion scale R of the dispersion on the character of the spatial non {locality of D (q;!) in the Anderson localization regime and, in particular, on the value of the correlation multifractal dimension D $_2$ of the electron wave functions near the mobility edge.

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1. In the last few years considerable attention has been focused on the problem of spatial dispersion (non{locality) of the kinetic coe cients of disordered systems in the Anderson localization regime [1{6]. The cause of such interest was the realization of the fact that the character of the q! { dependence of the generalized di usion coe cient D (q;!) near the mobility edge is intim ately connected to critical behavior of the electron wave functions and, in the end, is determined by the scenario of the metal (insulator transition [1,3]. Indeed, the Berezinskij { Gorkov localization criterion [7] requires that in the localized phase D (q;0) vanish simultaneously for all values of the wave number q, and, according to the one { parameter scaling hypothesis, the relation

D
$$(t;q;!) = b^2 dD (b^{1=} t;bq;b^d!);$$
 2 < d < 4 (1)

must be satisfed [8]. Here $t=(E-E_c)=E_c$ is the distance to the mobility edge E_c , b is a scaling factor, d is the space dimension, is the correlation length critical index.

There are two qualitatively di erent versions of the critical behavior of D (q;!) that obey these general requirem ents.

A coording to Chalker's hypothesis [1], the multifractal structure of the electron wave functions near the Anderson transition (t! 0 and/or!! 0) leads to an anom alously strong spatial dispersion of the generalized di usion coe cient, whose scale is R = m in (;L!)! 1, where / jtj is the correlation length, $L! / D(!)=! / ! ^{1=d}$ is the electron di usion length in a time of 1=! [1,2]. Depending on the relation between ; L! and q Chalker [1] distinguishes four main types of the asymptotic behavior:

$$D(q;!) = D_0 \frac{1}{R}^{!d_2^{8}} \frac{1}{(qR)^{d_2}} qR \frac{1}{qR} R = min(;L_!): (2)$$

Here D₀ is the D rudian di usion coe cient, l is the mean free path, is a critical index related to the correlation multifractal dimension of the wave functions D₂ (= d D₂) [2].

On the other hand, Suslov's sym m etry approach to the localization theory [4] predicts supression of the spatial dispersion of the di usion coe cient in the vicinity of the Anderson transition down to atom ic scales $_{\rm F}$. M ore recently, this conclusion was con med within the fram ework of a generalized formulation [5,6] of the self(consistent Vollhardt | W ol e theory [11]. A coording to [5,6], in the Anderson localization regime

$$D(q;!) = \frac{D(t;!)}{1 + (qR)^2}; \qquad qR \qquad 1;$$
 (3)

where the non{locality scale R / $\stackrel{p}{D_0}$ $\stackrel{}{}$ $\stackrel{}{}}$ $\stackrel{}{}$ $\stackrel{}{}}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}}$ $\stackrel{}}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}}$ $\stackrel{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}$ $\stackrel{}{}}$ $\stackrel{}{}$ $\stackrel{}$

In the survey by Suslov [3] it is pointed out that the absence of anom alously strong spatial dispersion of the generalized di usion one cient near the mobility edge does not contradict the concept of multifractality of the electron wave functions, it only indicate that the equality $= d + 2 \pmod{2}$ should be satisted. The well-{known Wegner's result $= 2 \pmod{2} \pmod{2}$ ly [9] is directly connected with the critical behavior of the inverse participation ratio. At the same time, the relation between this quantity and D (q;!) used in [1,2,10] cannot be considered correct for several reasons. Therefore, in our opinion, the above contradiction is only apparent. The same may be said about the results of numerical modelling = 12 + 0.15, = 1.3 + 0.2, = 1.5 + 0.3 [2] and = 1.3 + 0.2 [10] obtained by different methods for d = 3.

This dilemma, touching upon the fundamental notions of the Anderson localization, calls for both theoretical and experimental solution. In

 $^{^{1}}$ The detailed discussion of the basic arguments pro and conhypothesis = d 2 may be found in [3].

this letter we derive a material equation relating the current density in the spatially nonuniform case to the experimentally measured dierence of the electrochemical potentials, and propose a measuring scheme that allows one to obtain information on the degree of non {locality of the diusion coecient of charge carriers.

Applying the general equations of the linear response theory [12,13] to the problem under consideration, we obtain a material equation relating the current density to the electrochem ical potential gradient. for $q = k_F$ its Fourier representation has the form

$$j(q;!) = iqen_F D(q;!) (q;!) = iq(q;!)U(q;!) = e;$$
 (4)

where n_F is the density of states at the Ferm i level, (q;!) is the measured electrical conductivity connected with D (q;!) by the E instein relation. It should be emphasized that (q;!) is not K ubo's kinetic coe cient

$$e(q;!) = e^{2}n_{F} \frac{D(q;!)}{1 + i(q^{2}=!)D(q;!)};$$
 (5)

which, unlike (q;!) (see Eq. (4)), relates the total current density to the electrical eld acting in the system. It is in the uniform case (q = 0) only that (0;!) = e(0;!), and Eq. (5) coincides with the Einstein relation.

Eqs. (4) and (5) describe the non{local linear response of a spatially unbounded and hom ogeneous system. In the general case, the non{locality of m aterial equations is of a more complicated character. In the typical experimental situation, the sample has the shape of a plane{parallel slab of thickness L. In this case the diusion propagator of charge carriers \pounds (x;x⁰;!) is a solution of the equation

²The nonuniform spatial electron distribution results not only in perturbation of the electrical eld in the conductor, which is involved in ', but also in the appearance of the di usion term in the measured total current density. Just the latter term is the response of the system to the thermal perturbation.

with the open boundary conditions

$$\hat{\mathbf{G}}(\mathbf{x}; \mathbf{x}^0; !)_{\mathbf{x}; \mathbf{x}^0 = L = 2} = 0: \tag{7}$$

The integral kernel of this equation (non { local diusion coe cient) enters into the material equation that relates the electrical current to the electrochemical potential gradient (voltage drop)

$$I(x) = e^{2} n_{F} S \int_{L=2}^{\frac{L}{2}=2} dx (x; x^{0}; !) \frac{e}{e^{2} x^{0}} U(x^{0}) dx^{0};$$
 (8)

where S / L^d is the area of the sample cross section. The solution of the boundary problem (6), (7) in the absence of spatial dispersion (f (x;x 0 ;!) = D (!) (x x^{0}) is given by well{known m ethod of im ages [14]

$$\hat{G}(x;x^{0};!) = \sum_{n=-1}^{x^{1}} [G(x + x^{0} + 2nL;!) G(x + x^{0} + (2n + 1)L;!)];$$

G (x;!) =
$$\frac{1}{L} \frac{x}{q} = \frac{\exp(iqx)}{i! + q^2D(!)}$$
: (9)

Here G(x;!) is the di usion propagator of charge carriers in a spatially unbounded hom ogeneous system. We assume that the solution (9) holds true in the presence of spatial dispersion if its scale is small in comparison with the sample size (R L). In this case the integral kernel of the material equation (8) is expressed, by analogy with (9), in terms of the generalized di usion coe cient D (q;!) of the spatially unbounded and hom ogeneous system

$$\stackrel{f}{\mathbb{D}} (\mathbf{x}; \mathbf{x}^0; !) = \frac{2}{L} \sum_{n=0}^{t^1} \mathbb{D} (\overline{\mathbf{q}}_n; !) \sin \overline{\mathbf{q}}_n \mathbf{x} \sin \overline{\mathbf{q}}_n \mathbf{x}^0 + \mathbb{D} (\mathbf{q}_n; !) \cos \mathbf{q}_n \mathbf{x} \cos \mathbf{q}_n \mathbf{x}^0];$$
 (10)

where $\overline{q}_n = 2$ n=L and $q_n = (2n + 1)$ =L are discrete values of the wave numbers.

Taking into account that the voltage drop U (x) is an odd function of x, and the current strength I(x) = I is constant along the studied sample, we will represent them through the corresponding Fourier series. Then, upon substitution of (10) in the material equation (8), it is not dicult to not the expression for the voltage drop Fourier coe cient U $_n$. Finally the x {dependence of the voltage drop can be presented as the following Fourier series:

$$U(x) = \frac{4I}{LSe^{2}n_{F}} \sum_{n=0}^{x^{1}} \frac{(1)^{n+1}}{q_{D}^{2}D(q_{D};!)} \sin q_{n}x; \quad \dot{x}j < L=2: \quad (11)$$

3. When the di usion coe cient is independent of the wave number q_n the series (11) gives, for a nite{size conductor, the usual conductance definition $g(L;!) = L^{d-2}e^2n_FD$ (0;!) = L^{d-2} (!) and describes the linear x{ dependence of the voltage drop U (x) within the sample (jxj < L=2). The spatial non{locality of the generalized di usion coe cient D ($q_n;!$) changes the conductance de nition as:

$$\frac{1}{g(L;!)} = \frac{8}{LSe^{2}n_{F}} \frac{1}{n=0} \frac{1}{q_{P}^{2}D(q_{P};!)}$$
(12)

and results in a nonlinear x {dependence of the voltage drop (11). Thus, information on the spatial dispersion of the generalized disusion coescient of charge carriers D (q;!) can be obtained by measuring the nonlinear part of U(x) (11):

$$U(x) = U(x) \frac{2x}{L}U(L=2)$$
: (13)

Consider a sample in the form of a plane{parallel slab of thickness L R (R is the spatial non { locality scale}) with ideal ohm is contacts on the opposite surfaces and with two potential measuring probes which symmetrically located at a distance x from the mid{plane (see Fig. 1 (a)). It is best to situate them easuring probes near the x_{max} points where U (x) reaches its maximum value U $_{max}$. A nother pair of potential probes, the role of which is played here by the ideal ohm is contacts, are necessary for measuring the non { linear part of the voltage drop (13).

Substituting (3) into (11), (13) yields U(x) = 0. Strictly speaking, this equality is ful led in the case of ideal compensation of the linear part of the voltage drop. In any case, however, the measured signal is small in pa-1. The nonzero contribution to U(x) comes only from ram eter R =L the nontrivial q{dependence of the generalized di usion coe cient from (2). Fig. 1 (b) shows typical dependences of U (x) calculated using linear interpolation between Chalker's asymptotic formulas (2) for the inverse di usion coe cient 1=D (q;!) at qR 1 and qR 1. In this case x_{max} does not depend on the scale of spatial non { locallity of D (q;!) and assum es values on $(0.70 \quad 0.76)L=2 \text{ for } = 1.1$ 1:5. The non { linear part the interval x_{max} U $_{\text{m ax}}$ calculated at these points has the following asym ptotic behaviors

$$U_{\text{max}} / \frac{R^{!}}{L} / \stackrel{8}{\cdot} ! \stackrel{=d}{\cdot} ; L_{!} ; L_{!} ; L_{!} ; (14)$$

Two ways for measuring the signal (14) may be suggested. The rst is to analyze the frequency dependence of $U_{max}(!)$ in a sample with a xed

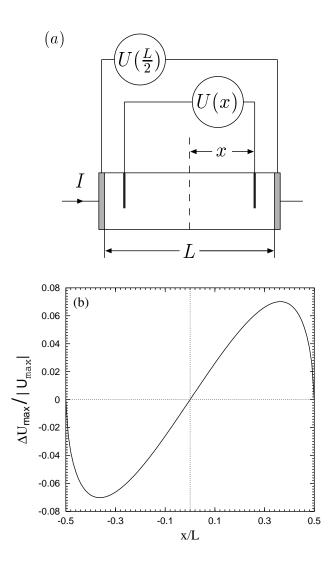


Figure 1: (a) The scheme of the measurement of the nonlinear part of the voltage drop (here is depicted a longitudinal section of investigated sample); (b) Typical dependence of the nonlinear part of the voltage drop on the potential probe position x. Curve is calculated using Chalker's asymptotic formulas (2) for = 1.3 and for R = L = 0.1.

disorder level in a sm all enough vicinity of the mobility edge on the metallic side of transition (tj 1). A coording to (14) and the predictions of Ref. [1], as the frequency decreases, an increase in U_{max} / ! =d (! !c) should be observed until saturation is reached at U_{max} / (=L) (! !c). The typical frequency !c is determined by the relation $L_{!c}$ = or h!c $_{F}$ $^{d}n_{F}$ $^{1}tj^{d}$, where $_{F}$ is de B roglie's wave length at the Fermi level.

The second way is to measure the dependence of U $_{max}$ (14) on a dimension-less distance t to the mobility edge E_c at a xed frequency ! . The stress { tuning technique [15] seems to be the simplest method of changing t in the vicinity of E_c . A very suitable material for such measurements is SiP, in which this technique makes it possible to attain tj 10 3 [15]. According to (14) and the predictions of Ref. [1], as t decreases, an increase in

 U_{max} / t (t t_i) should be observed until saturation is reached at U_{max} / (L_i=L) (t t_i). Here the typical value t_i is determined by the relation L_i = or ${}^d_F n_F h!$ †_i j^d.

Such dependences obtained by Eqs. (11), (13) using the interpolation $R^{-1} = {}^{-1} + L_1^{-1}$ for the non {locality scale, are plotted in Fig. 2 (a,b). Since in a su ciently small vicinity of the mobility edge the non {locality scale of D (q;!) (2) takes on anomalously large values $R = m in (L_1;)$, the value of U_{max} (14) is quite accessible form easurem ent. The estimates show that for Sip samples with the typical phosphorus concentrations np 10^{18} cm 3 and for really attainable values † j 10² 10^{3} , sim ilar dependences of U _{max} (see Eq. (14) and Fig. 2) should be observed in the frequency region accessible for probe m easurem ents. For example, at t 10³ the typical frequence 10ts 1 (see Fig. 2 (a)), and the corresponding correlation value is! 103 lengths are of order L ! $10^3 10^2 \text{cm}$.

So, we believe that the existence [1,2] or supression [4{6] of the anom alous spatial dispersion of the generalized di usion coe cient near the Anderson transition can be veri ed experim entally.

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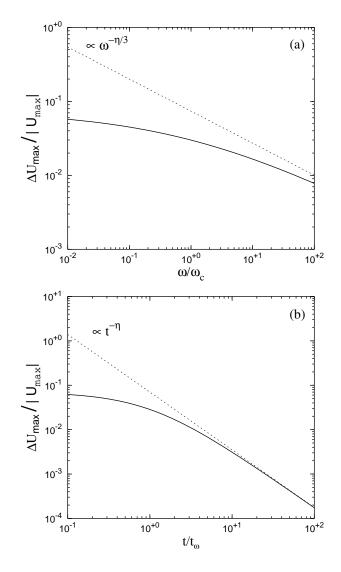


Figure 2: Typical dependences of U_{max} on the frequency, !, (a) and dimensionless distance from the mobility edge, t, (b) calculated by Eqs. (11), (13) using Chalker's expressions (2) for = 1:3. D ashed straight lines depict the asymptotic behavior predicted by Eq. (14).

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